DS3585-4.3

MA9167

RADIATION HARD 16384 x 1 BIT STATIC RAM

The MA9167 16k Static RAM is configured as 16384 x 1 bits and manufactured using GPS's CMOS-SOS high performance, radiation hard, 1.5µm technology.

The device has separate input and output terminals controlled by Chip Select and Write Enable. The design uses a 6 transistor cell and has full static operation with no clock or timing strobe required. Address input buffers are deselected when Chip Select is in the high state.

See Application Note "Overview of the GPS Radiation Hard 1.5µm CMOS/SOS SRAM Range".

$\overline{CS}$	$\overline{WE}$	Mode	V_{DD} Current	Output Pin
H	X	Deselected	I_{SB2}	High Z
L	H	Read	I_{SB1}	D_{OUT}
L	L	Write	I_{SB1}	High Z

Figure 1: Truth Table

FEATURES

- 1.5µm CMOS-SOS Technology
- Latch-up Free
- Fast Access Time 35ns Typical
- Total Dose 10^6 Rad(Si)
- Transient Upset >10^{11} Rad(Si)/sec
- SEU 4.3 x 10^{-11} Errors/bitday
- Single 5V Supply
- All Inputs and Outputs Fully TTL or CMOS Compatible
- Fully Static Operation
- Three State Output
- Low Standby Current 100µA Typical
- -55°C to +125°C Operation

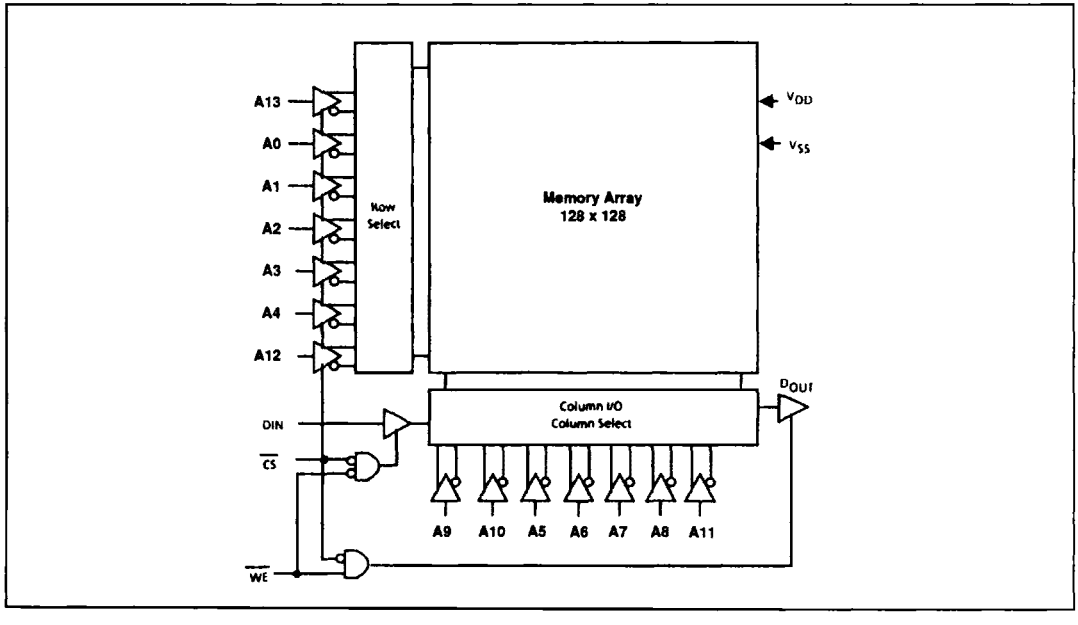


Figure 2: Block Diagram

CHARACTERISTICS AND RATINGS

Symbol	Parameter	Min.	Max.	Units
V_{CC}	Supply Voltage	-0.5	7.0	V
V_I	Input Voltage	-0.3	V_{DD}+0.3	V
T_A	Operating Temperature	-55	125	°C
T_S	Storage Temperature	-65	150	°C

Stresses above those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions, or at any other condition above those indicated in the operations section of this specification, is not implied Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Figure 3: Absolute Maximum Ratings

Notes for Tables 4 and 5:
Characteristics apply to pre radiation at T_A = -55°C to +125°C with V_{DD} = 5V ±10% and to post 100k Rad(Si) total dose radiation at T_A = 25°C with V_{DD} = 5V ±10% (characteristics at higher radiation levels available on request). GROUP A SUBGROUPS 1, 2, 3.

Symbol	Parameter	Conditions (Option)	Min.	Typ.	Max.	Units
V_{DD}	Supply voltage	-	4.5	5.0	5.5	V
V_{IH}	Logical '1' Input Voltage	- (TTL) (CMOS)	2.0 0.8 V_{DD}	- -	V_{DD} V_{DD}	V V
V_{IL}	Logical '0' Input Voltage	- (TTL) (CMOS)	V_{SS} V_{SS}	- -	0.8 0.2 V_{DD}	V V
V_{OH1}	Logical '1' Output Voltage	I_{OH1} = -4mA	2.4	-	-	V
V_{OH2}	Logical '1' Output Voltage	I_{OH2} = -3mA	V_{DD} -0.5	-	-	V
V_{OL}	Logical '0' Output Voltage	I_{OL} = 8mA	-	-	0.4	V
I_{LI}	Input Leakage Current	V_{IN} = V_{DD} or V_{SS} All inputs	-	-	±10	µA
I_{LO}	Output Leakage Current	Chip disabled, V_{OUT} = V_{DD} or V_{SS}	-	-	±10	µA
I_{SB1}	Selected Static Current (CMOS)	All inputs = V_{DD} -0.2V except $\overline{CS}$ = V_{SS} +0.2V	-	0.1	5	mA
I_{DD}	Dynamic Operating Current (CMOS)	f_{RC} = 1MHz, all inputs switching, V_{IH} = V_{DD} -0.2V	-	3	8	mA
I_{SB2}	Standby Supply Current	$\overline{CS}$ = V_{DD} -0.2V	-	0.1	5	mA

Figure 4: Electrical Characteristics

Symbol	Parameter	Conditions (Option)	Min.	Typ.	Max.	Units
V_{DR}	V_{CC} for Data Retention	$\overline{CS}$ = V_{DR}	2.0	-	-	V
I_{DDR}	Data Retention Current	$\overline{CS}$ = V_{DR}, V_{DR} = 2.0V	-	0.05	2	mA

Figure 5: Data Retention Characteristics

AC CHARACTERISTICS

Conditions of Test for Tables 5 and 6:
1. Input pulse = V_{SS} to 3.0V (TTL).
2. Times measurement reference level = 1.5V.
3. Input Rise and Fall times ≤5ns.
4. Output load 1TTL gate and CL = 60pF.
5. Transition is measured at ±500mV from steady state.
6. This parameter is sampled and not 100% tested.

Notes for Tables 6 and 7:
Characteristics apply to pre-radiation at T_A = -55°C to +125°C with V_{DD} = 5V±10% and to post 100k Rad(Si) total dose radiation at T_A = 25°C with V_{DD} = 5V ±10%. GROUP A SUBGROUPS 9, 10, 11.

Symbol	Parameter	MAX9167X70 Min	Max	Units
T_{AVAVR}	Read Cycle Time	70	-	ns
T_{AVOV}	Address Access Time	-	70	ns
T_{ELOV}	Chip select Access time	-	70	ns
T_{ELOX} (5,6)	Chip Selection to Output in Low Z	15	-	ns
T_{EHQZ} (5,6)	Chip Deselection to Output in High Z	0	20	ns
T_{AXOX}	Output Hold from Address change	30	-	ns

Figure 6: Read Cycle AC Electrical Characteristics

Symbol	Parameter	MAX9167X70 Min	Max	Units
T_{AVAVW}	Write Cycle Time	50	-	ns
T_{ELWH}	Chip Selection to End of Write	50	-	ns
T_{AVWH}	Address Valid to End of Write	50	-	ns
T_{AVWL}	Address Set Up Time	0	-	ns
T_{WLWH}	Write Pulse Width	35	-	ns
T_{WHAV}	Write Recovery Time	0	-	ns
T_{WLQZ} (5,6)	Wnte to Output in High Z	0	20	ns
T_{DVWH}	Data to Write Time Overlap	25	-	ns
T_{WHDX}	Data Hold from Write	0	-	ns
T_{WHQX} (5,6)	Output Active from End to Write	0	20	ns

Figure 7: Write Cycle AC Electrical Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
C_{IN}	Input Capacitance	V_I = 0V	-	3	5	pF
C_{OUT}	Output Capacitance	$V_{I/O}$ = 0V	-	5	7	pF

Note: T_A = 25°C and f = 1MHz. Data obtained by characterisation or analysis; not routinely measured.

Figure 8: Capacitance

Symbol	Parameter	Conditions
F_T	Basic Functionality	V_{DD} = 4.5V - 5.5V, FREQ = 1MHz $V_{IL} = V_{SS}$, $V_{IH} = V_{DD}$, $V_{OL} \leq 1.5V$, $V_{OH} \geq 1.5V$ TEMP = -55°C to +125°C, GPS PATTERN SET GROUP A SUBGROUPS 7, 8A, 8B

Figure 9: Functionality

Subgroup	Definition
1	Static characteristics specified in Tables 4 and 5 at +25°C
2	Static characteristics specified in Tables 4 and 5 at +125°C
3	Static characteristics specified in Tables 4 and 5 at -55°C
7	Functional characteristics specified in Table 9 at +25°C
8A	Functional characteristics specified in Table 9 at +125°C
8B	Functional characteristics specified in Table 9 at -55°C
9	Switching characteristics specified in Tables 6 and 7 at +25°C
10	Switching characteristics specified in Tables 6 and 7 at +125°C
11	Switching characteristics specified in Tables 6 and 7 at -55°C

Figure 10: Definition of Subgroups

TIMING DIAGRAMS

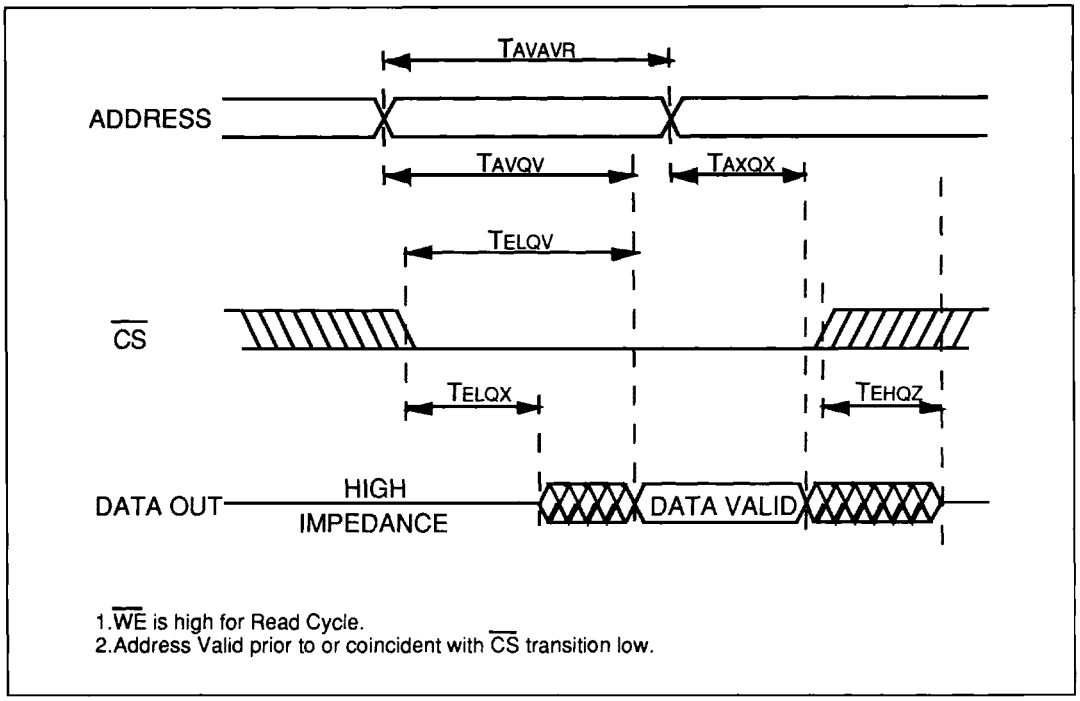


Figure 11: Read Cycle 1

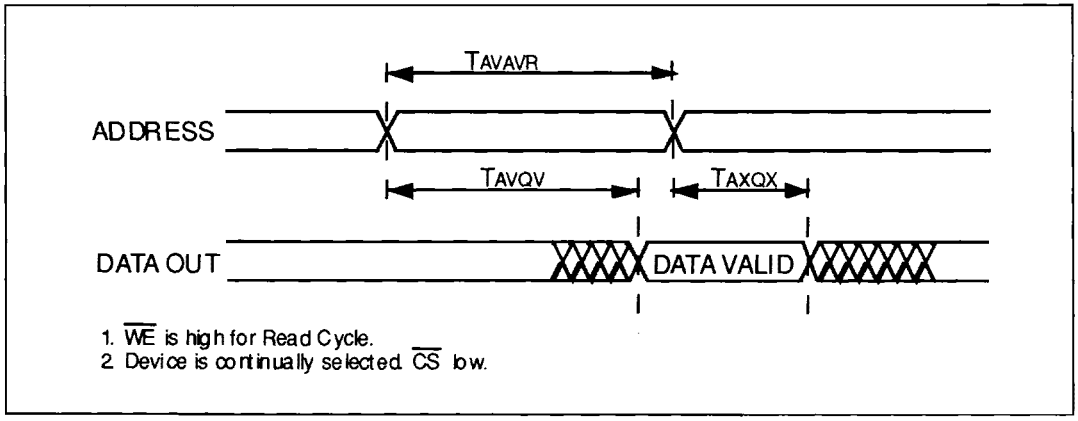
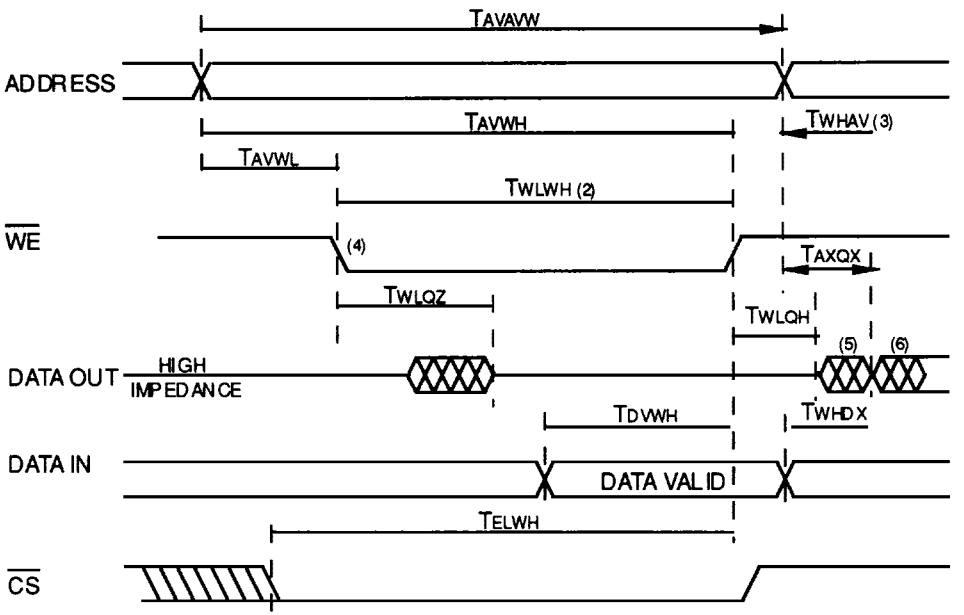


Figure 12: Read Cycle 2

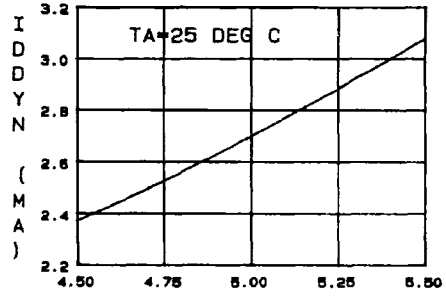


1. $\overline{WE}$ must be high during all address transitions.
2. A write occurs during the overlap (T_{WLWH}) of a low $\overline{CS}$ and a low $\overline{WE}$.
3. T_{WHAV} is measured from either $\overline{CS}$ or $\overline{WE}$ going high whichever is the earlier, to the end of the write cycle.
4. If the $\overline{CS}$ low transition occurs simultaneously with, or after, the $\overline{WE}$ low transition, the output remains in the high impedance state.
5. DATA OUT is the write data of the current cycle, if selected.
6. DATA OUT is the read data of the next address, if selected.

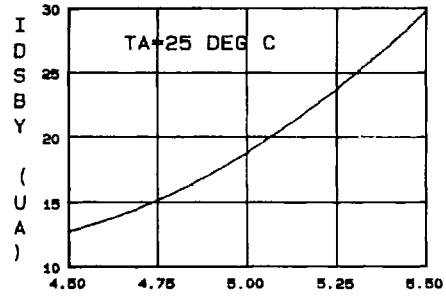
Figure 13: Write Cycle

TYPICAL PERFORMANCE CHARACTERISTICS MAx9167x70

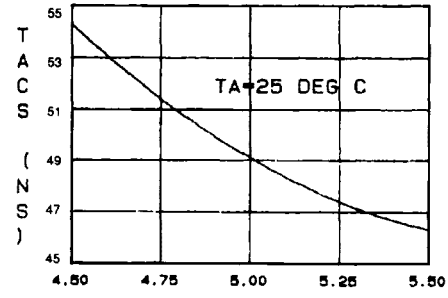
DYNAMIC CURRENT VS SUPPLY VOLTAGE



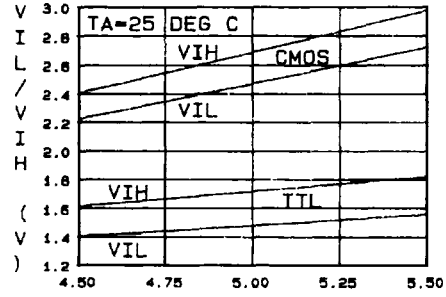
STANDBY CURRENT VS SUPPLY VOLTAGE



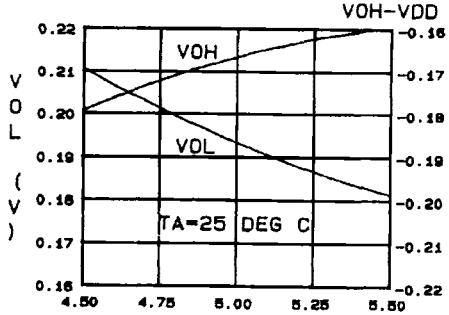
CS ACCESS TIME VS SUPPLY VOLTAGE



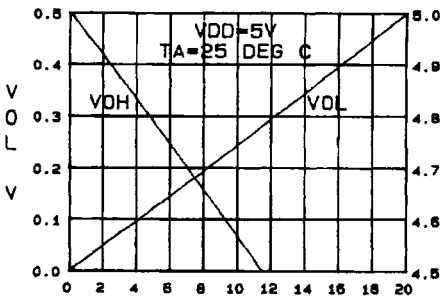
INPUT LEVELS VS SUPPLY VOLTAGE



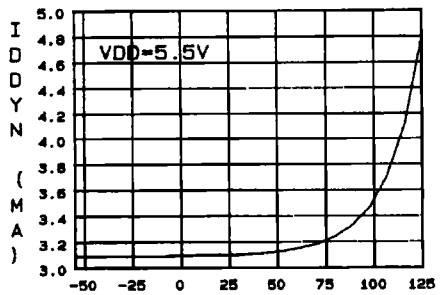
OUTPUT LEVELS VS SUPPLY VOLTAGE



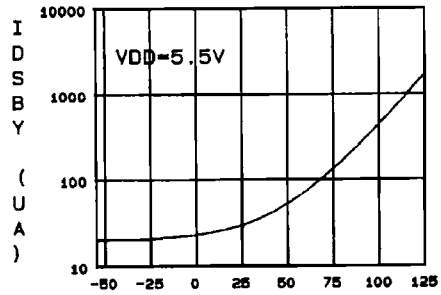
OUTPUT VOLTAGE VS CURRENT



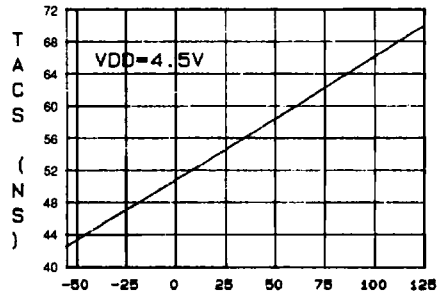
DYNAMIC CURRENT VS TEMPERATURE



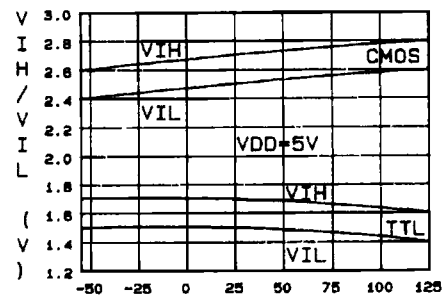
STANDBY CURRENT VS TEMPERATURE



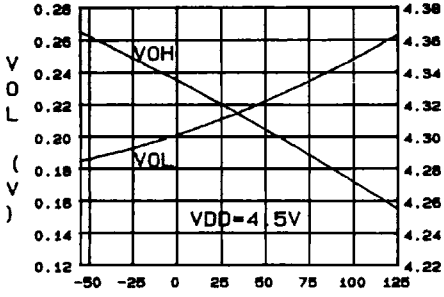
CS ACCESS TIME VS TEMPERATURE



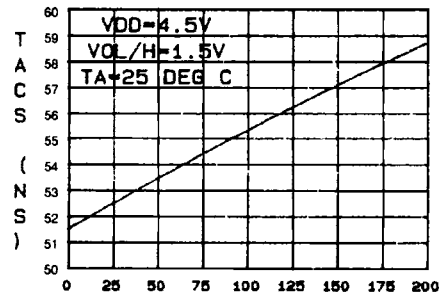
INPUT LEVELS VS TEMPERATURE



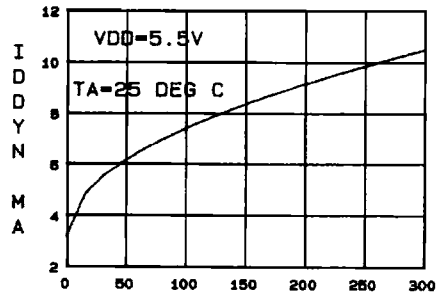
OUTPUT LEVELS VS TEMPERATURE



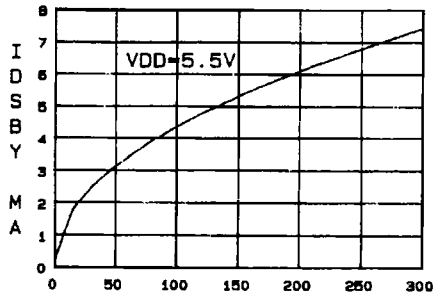
CS ACCESS TIME VS OUTPUT LOAD



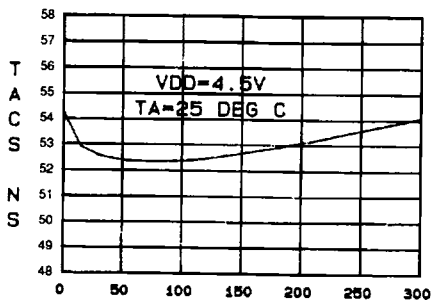
DYNAMIC CURRENT VS RADIATION



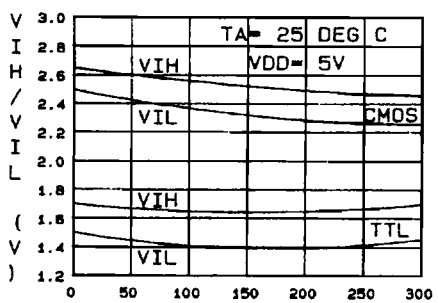
STANDBY CURRENT VS RADIATION



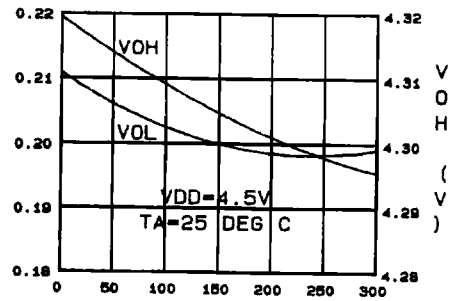
CS ACCESS TIME VS RADIATION



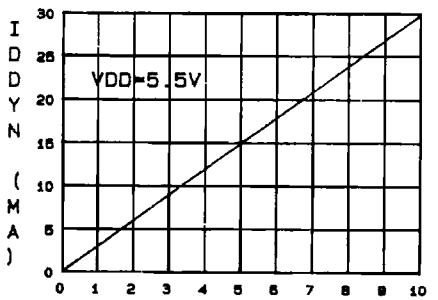
INPUT LEVELS VS RADIATION



OUTPUT LEVELS VS RADIATION



DYNAMIC CURRENT VS FREQUENCY



PIN ASSIGNMENTS

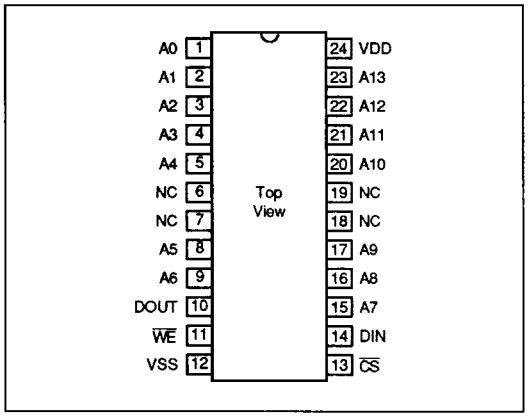


Figure 14: 24-Pin Ceramic DIL (Solder Seal) - Package Style C (Pin Assignment Option 1)

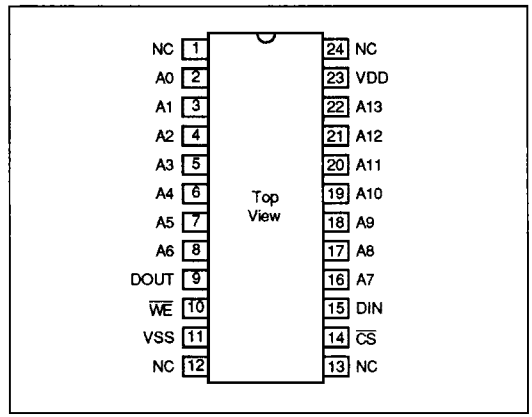


Figure 15: 24-Pin Ceramic DIL (Solder Seal) - Package Style F (Pin Assignment Option 2)

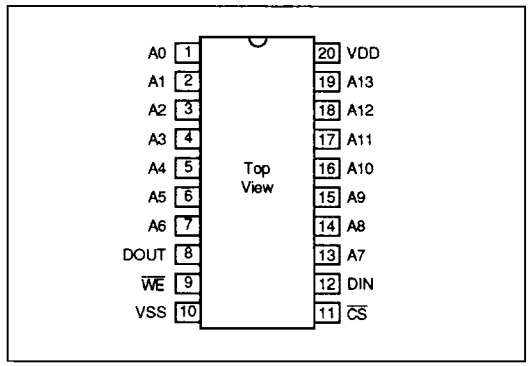


Figure 16: 20-Pin Ceramic DIL(Solder Seal) - Package Style C

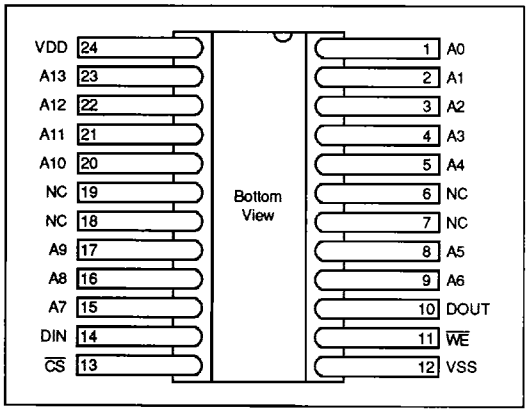


Figure 17: 24-Lead Ceramic Flatpack (Solder Seal) - Package Style F (Pin Assignment Option 1)

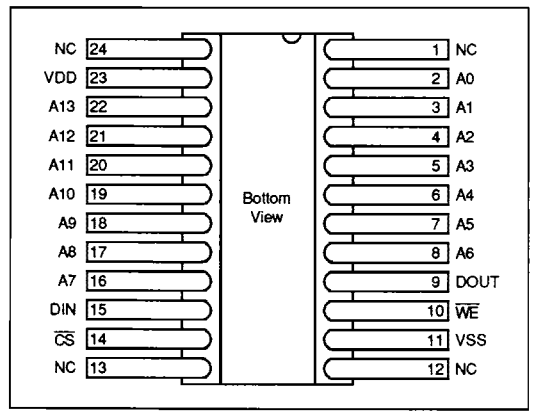
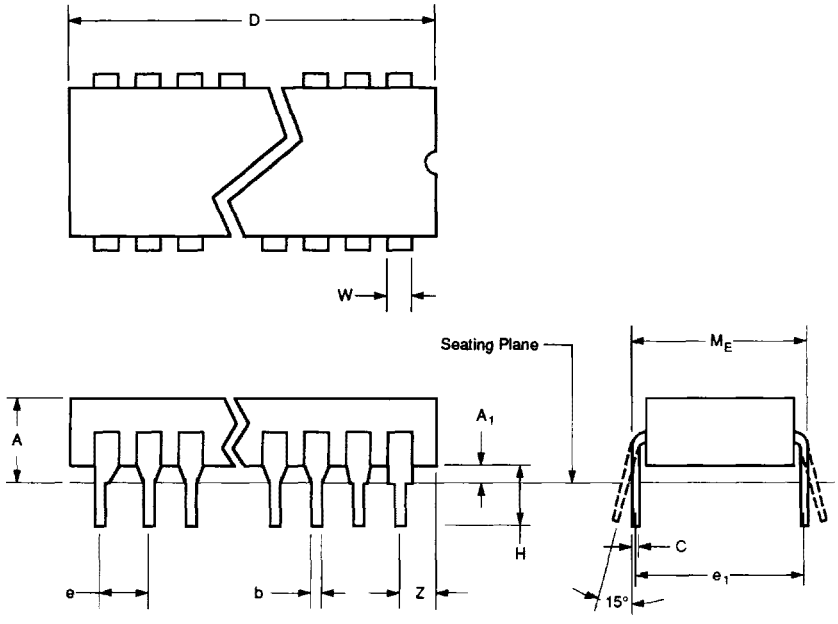


Figure 18: 24-Lead Ceramic Flatpack (Solder Seal) - Package Style F (Pin Assignment Option 2)

PACKAGE OUTLINES



20-Lead

Ref	Millimetres			Inches		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	-	-	5.715	-	-	0.225
A1	0.38	-	1.53	0.015	-	0.060
b	0.35	-	0.59	0.014	-	0.023
c	0.20	-	0.36	0.008	-	0.014
D	23.11	-	25.65	0.910	-	1.010
e	-	2.54 Typ.	-	-	0.100 Typ.	-
e1	-	8.13 Typ.	-	-	0.300 Typ.	-
H	4.71	-	5.38	0.185	-	0.212
Me	-	-	7.95	-	-	0.313
Z	-	-	1.27	-	-	0.050
W	-	-	1.53	-	-	0.060

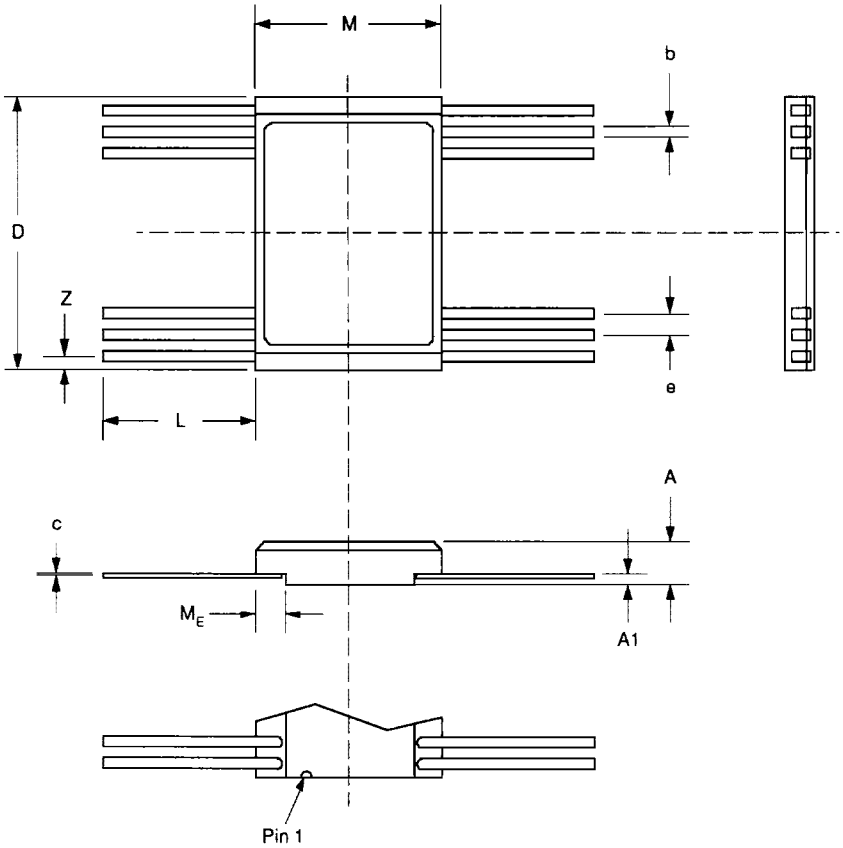
XG483

24-Lead

Ref	Millimetres			Inches		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	-	-	5.715	-	-	0.225
A1	0.38	-	1.53	0.015	-	0.060
b	0.35	-	0.59	0.014	-	0.023
c	0.20	-	0.36	0.008	-	0.014
D	-	-	30.79	-	-	1.212
e	-	2.54 Typ.	-	-	0.100 Typ.	-
e1	-	15.24 Typ.	-	-	0.600 Typ.	-
H	4.71	-	5.38	0.185	-	0.212
Me	-	-	15.90	-	-	0.626
Z	-	-	1.27	-	-	0.050
W	-	-	1.53	-	-	0.060

XG403

Figure 19: 20/24-Lead Ceramic DIL (Solder Seal) - Package Style C



Ref	Millimetres			Inches		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	-	-	3.07	-	-	0.121
A1	0.66	-	-	0.026	-	-
b	0.38	-	0.48	0.015	-	0.019
c	0.08	-	0.152	0.003	-	0.006
D	14.99	-	15.50	0.590	-	0.610
e	-	2.54	-	-	0.050	-
L	6.73	-	7.75	0.265	-	0.305
M	9.96	-	10.36	0.392	-	0.408
Me	7.6	-	-	0.30	-	-
Z	0.13	-	1.14	0.005	-	0.045

XG544

Figure 20: 24-Lead Ceramic Flatpack (Solder Seal) - Package Style F

Function	Pin Number			Via	Static 1	Static 2	Dynamic	Radiation
	D and F (24 pin)		D(20 pin)					
	Option 1	Option 2						
A0	1	2	1	R	5V	0V	F0	5V
A1	2	3	2	R	5V	0V	F1	5V
A2	3	4	3	R	5V	0V	F2	5V
A3	4	5	4	R	5V	0V	F3	5V
A4	5	6	5	R	5V	0V	F4	5V
A5	8	7	6	R	5V	0V	F5	5V
A6	9	8	7	R	5V	0V	F6	5V
DOUT	10	9	8	R	5V	0V	LOAD	5V
WEB	11	10	9	R	5V	0V	F14	5V
VSS	12	11	10	Direct	0V	0V	0V	0V
CSB	13	14	11	R	5V	0V	0V	5V
DIN	14	15	12	R	5V	0V	F15	5V
A7	15	16	13	R	5V	0V	F7	5V
A8	16	17	14	R	5V	0V	F8	5V
A9	17	18	15	R	5V	0V	F9	5V
A10	20	19	16	R	5V	0V	F10	5V
A11	21	20	17	R	5V	0V	F11	5V
A12	22	21	18	R	5V	0V	F12	5V
A13	23	22	19	R	5V	0V	F13	5V
VDD	24	23	20	Direct	5V	5V	5V	5V

1. FO = 150KHz, F1 = FO/2, F2 = FO/4, F3 = FO/8 etc.
2. Static 1 , Static 2 and Dynamic R = 4K7
3. Radiation R = 10K.

Figure 21: Burnin and Radiation Configuration

RADIATION TOLERANCE

Total Dose Radiation Testing

For product procured to guaranteed total dose radiation levels, each wafer lot will be approved when all sample devices from each lot pass the total dose radiation test.

The sample devices will be subjected to the total dose radiation level (Cobalt-60 Source), defined by the ordering code, and must continue to meet the electrical parameters specified in the data sheet. Electrical tests, pre and post irradiation, will be read and recorded.

GEC Plessey Semiconductors can provide radiation testing compliant with MIL-STD-883 test method 1019, Ionizing Radiation (Total Dose).

Total Dose (Basic function)	$1x10^6$ Rad(Si)
Total Dose (Function to specification)	$1x10^6$ Rad(Si)
Transient Upset	$>10^{11}$ Rad(Si)/sec
Neutron Hardness (Function to specification)	$>10^{15}$ neutrons/cm^2
Single Event Upset (GSO 10% worst case)	$4.3x10^{-11}$ errors/bitday
Latch-up	Not possible

Figure 22: Typical Radiation Hardness Parameters

SINGLE EVENT UPSET CHARACTERISTICS

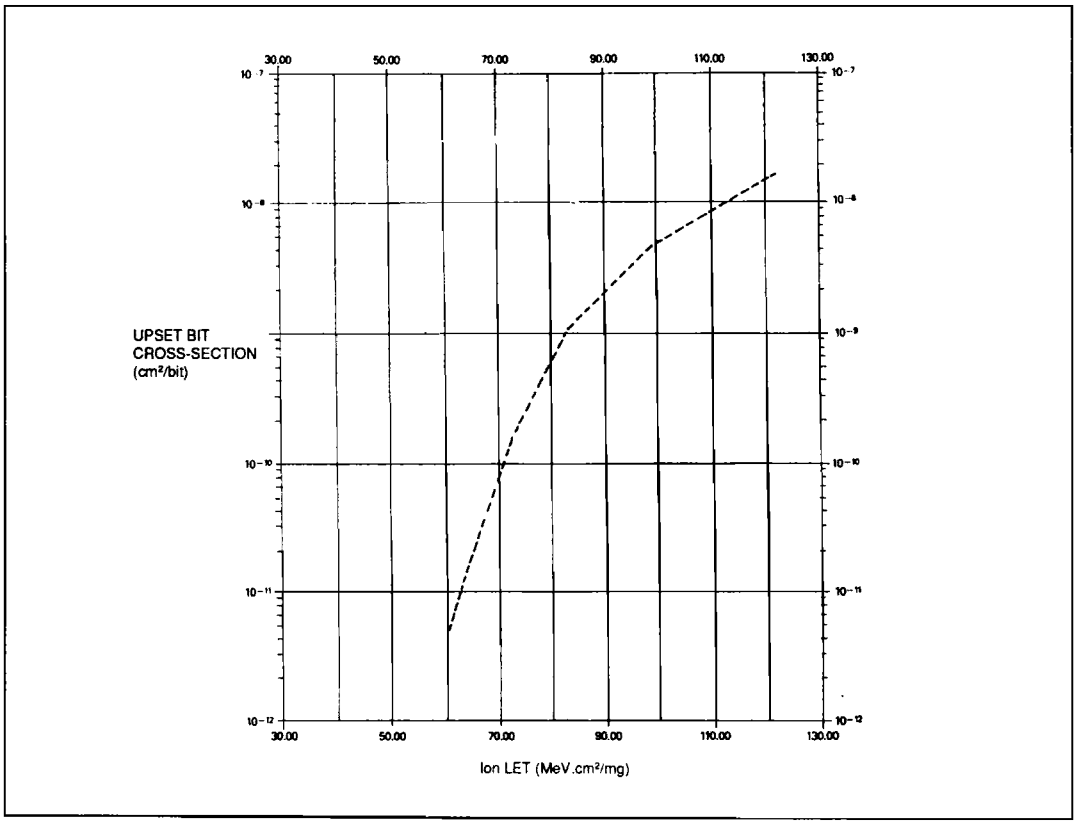
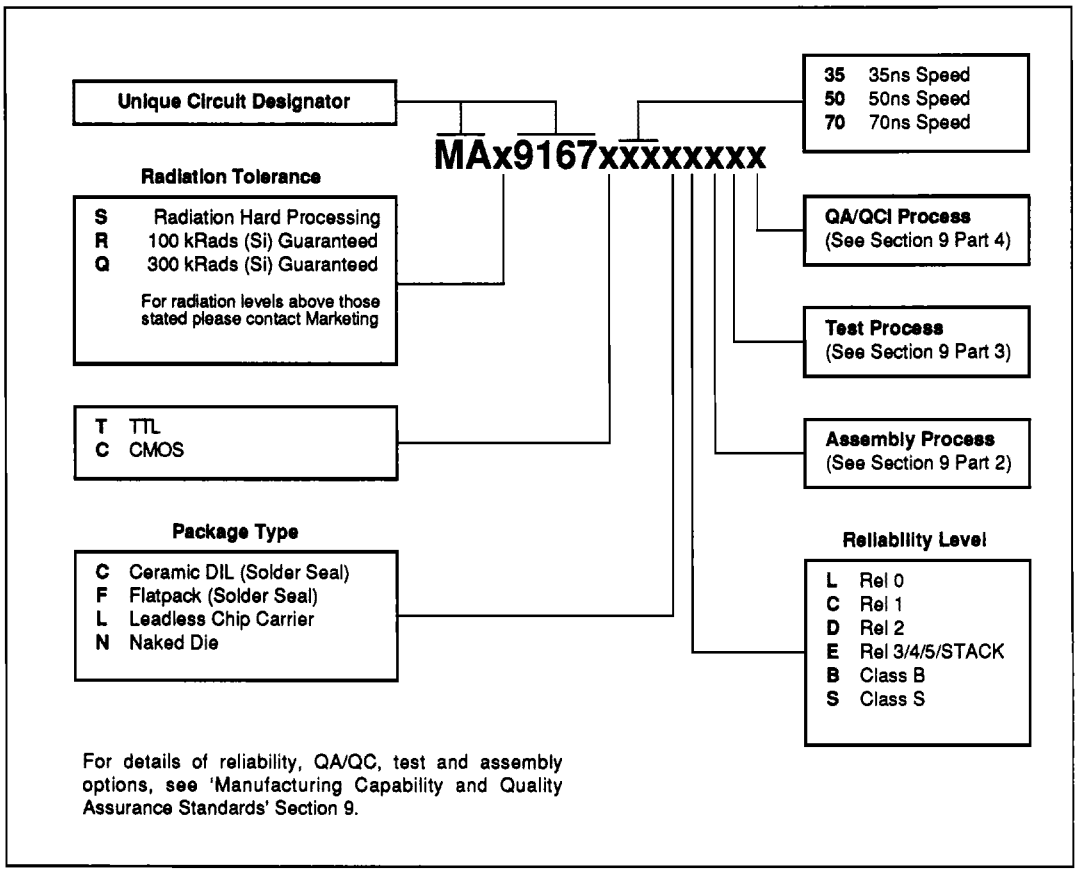


Figure 23: Typical Per-Bit Upset Cross-Section vs Ion LET

ORDERING INFORMATION



For details of reliability, QA/QC, test and assembly options, see 'Manufacturing Capability and Quality Assurance Standards' Section 9.